

What is claimed is:

1. A microwave tunable device, comprising:
a substrate; and

5 a ferroelectric/dielectric $(\text{Ba}_{1-x}\text{Sr}_x)\text{TiO}_3$ (BST) thin film
of a (111) direction which is formed on the substrate.

2. The microwave tunable device as recited in claim 1,
wherein the ferroelectric/dielectric BST thin film is grown by
10 performing a laser ablation.

3. The microwave tunable device as recited in claim 1,
wherein the substrate is an MgO substrate.